

## 2SB1061

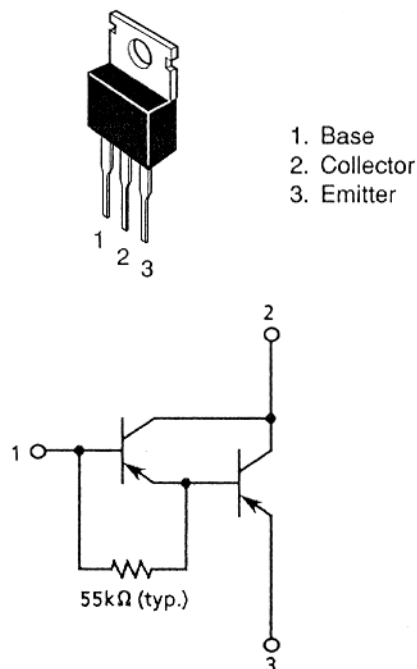
**Silicon PNP Triple Diffused  
Low Frequency Power Amplifier**

### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	$V_{CBO}$	-300	V
Collector to emitter voltage	$V_{CEO}$	-300	V
Emitter to base voltage	$V_{EBO}$	-7	V
Collector current	$I_C$	-0.3	A
Collector peak current	$i_{C(peak)}$	-0.6	A
Collector power dissipation	$P_C$	1.5	W
	$P_C^{*1}$	15	
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

Note: 1. Value at  $T_C = 25^\circ\text{C}$ .

TO-220 AB



### Electrical Characteristics (Ta = 25°C)

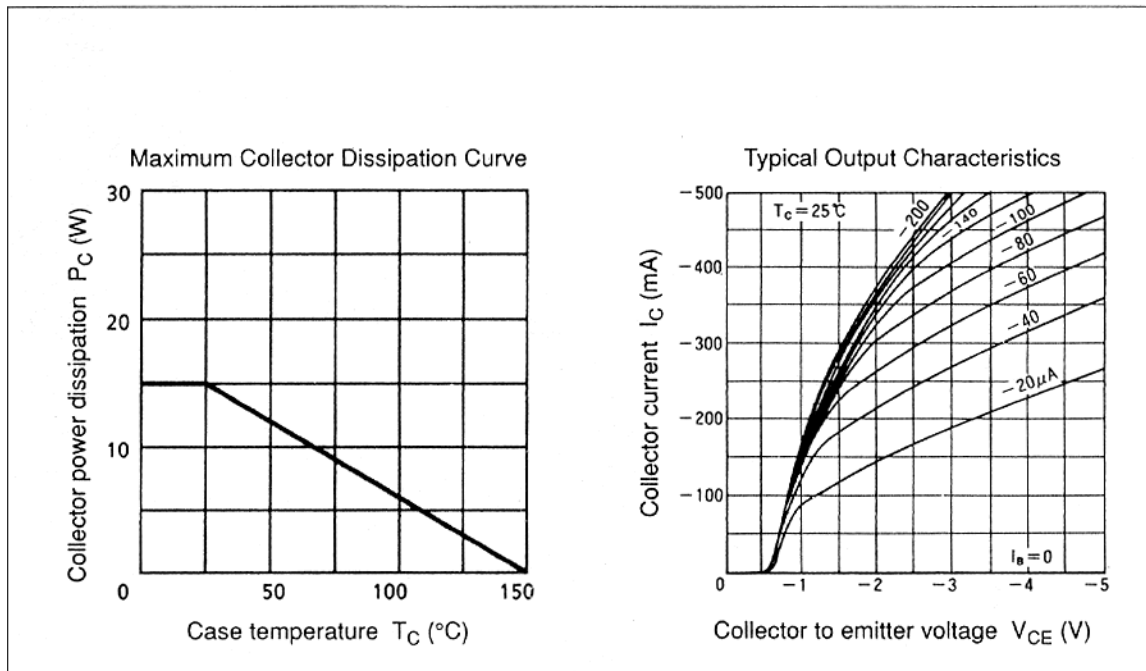
Item	Symbol	Min	Typ	Max	Unit	Test condition
Collector to base breakdown voltage	$V_{(BR)CBO}$	-300	—	—	V	$I_C = -1 \text{ mA}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-300	—	—	V	$I_C = -10 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	—	—	V	$I_E = -1 \text{ mA}, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	-10	$\mu\text{A}$	$V_{CB} = -300 \text{ V}, I_E = 0$
	$I_{CEO}$	—	—	-10		$V_{CE} = -60 \text{ V}, R_{BE} = \infty$
Emitter cutoff current	$I_{EBO}$	—	—	-10	$\mu\text{A}$	$V_{EB} = -5 \text{ V}, I_C = 0$
DC current transfer ratio	$h_{FE1}$	1000	—	—		$V_{CE} = -1.5 \text{ V}, I_C = -20 \text{ mA}^{*1}$
	$h_{FE2}$	1500	—	—		$V_{CE} = -1.5 \text{ V}, I_C = -100 \text{ mA}^{*1}$

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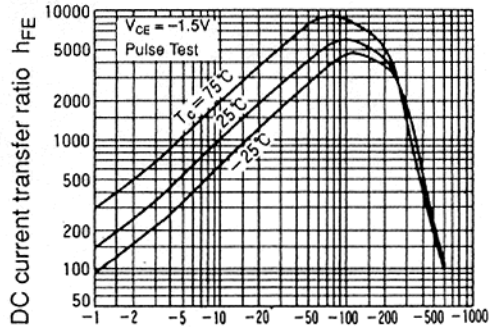
### Electrical Characteristics (Ta = 25°C) (cont)

Item	Symbol	Min	Typ	Max	Unit	Test condition
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-1.5	V	$I_C = -100 \text{ mA}, I_B = -0.2 \text{ mA}^1$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	-2.0	V	$I_C = -100 \text{ mA}, I_B = -0.2 \text{ mA}^1$

Note: 1. Pulse Test.

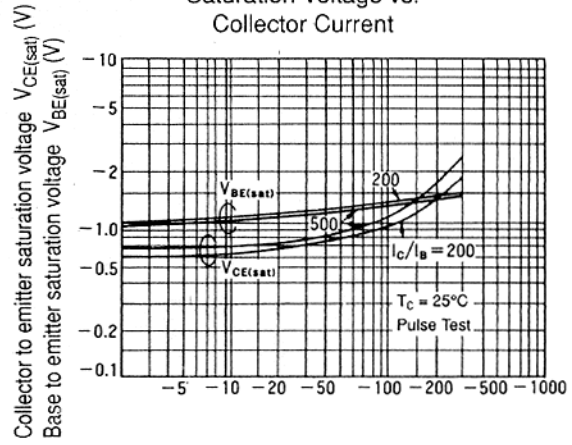


DC Current Transfer Ratio vs. Collector Current



Collector current  $I_C$  (mA)

Saturation Voltage vs. Collector Current



Collector current  $I_C$  (mA)

Transient Thermal Resistance

